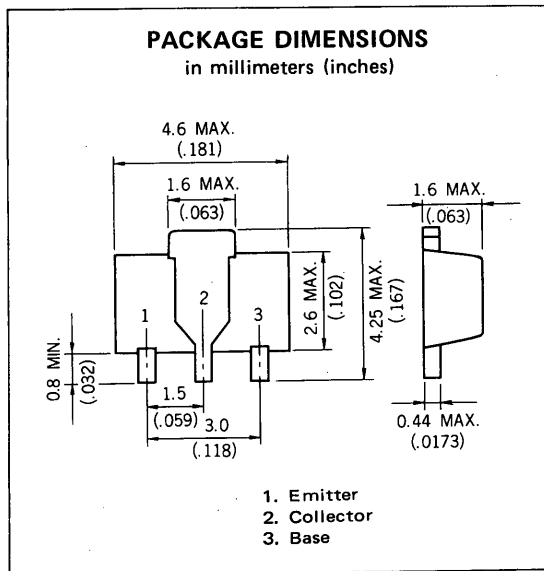


PNP SILICON EPITAXIAL TRANSISTOR
POWER MINI MOLD

DESCRIPTION

The 2SB798 is designed for audio frequency power amplifier application, especially in Hybrid Integrated Circuits.



FEATURES

- World Standard Miniature Package : SOT-89
- Low Collector Saturation Voltage : $V_{CE(sat)} < -0.4$ V ($I_C = -1.0$ A, $I_B = -100$ mA)
- Excellent DC Current Gain Linearity : $h_{FE} = 100$ TYP. ($V_{CE} = -1.0$ V, $I_C = -1.0$ A)
- Complements to NPN type 2SD999

ABSOLUTE MAXIMUM RATINGS ($T_a = 25$ °C)

Maximum Voltages and Currents

Collector to Base Voltage	V_{CB0}	-30	V
Collector to Emitter Voltage	V_{CEO}	-25	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current (DC)	I_C	-1.0	A
Collector Current (Pulse)*	I_C	-1.5	A

Maximum Power Dissipation

Total Power Dissipation at 25 °C Ambient Temperature**	P_T	2.0	W
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Maximum Temperatures

Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 to +150	°C

*PW ≤ 10 ms, Duty Cycle ≤ 50 %

**When mounted on ceramic substrate of 16 cm² x 0.7 mm

ELECTRICAL CHARACTERISTICS ($T_a = 25$ °C)

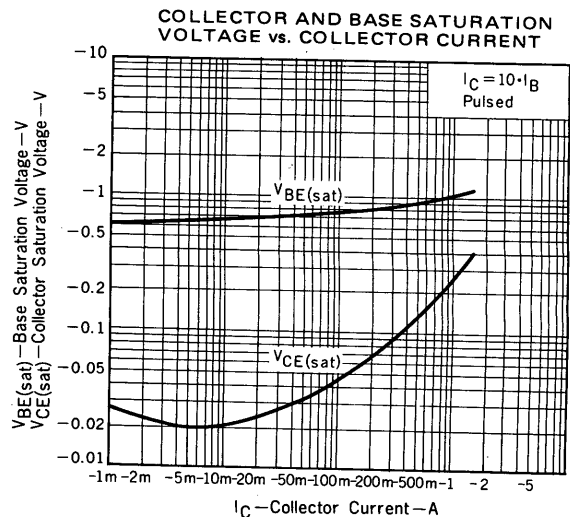
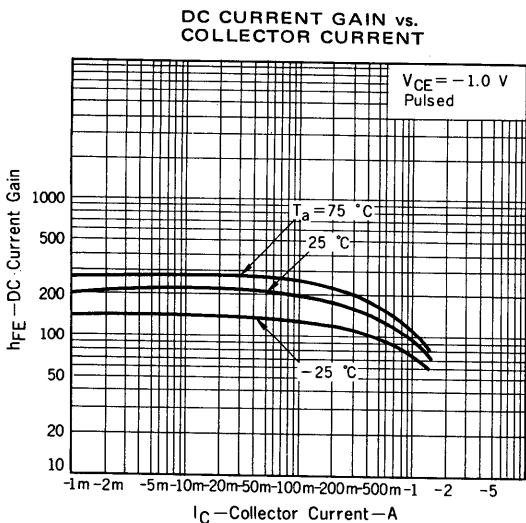
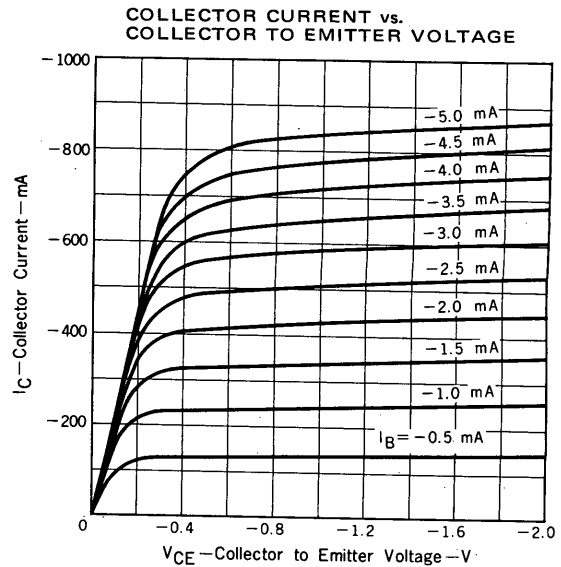
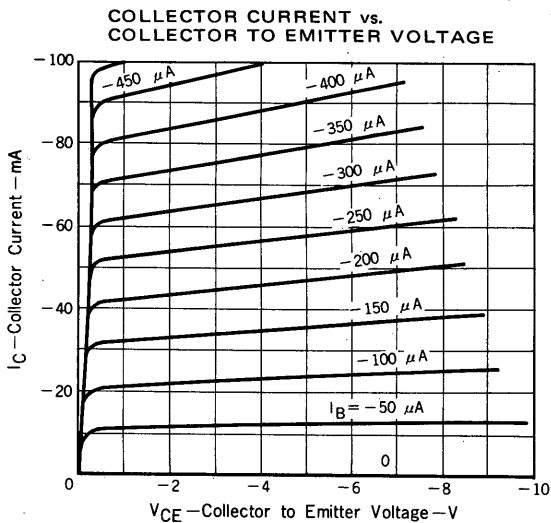
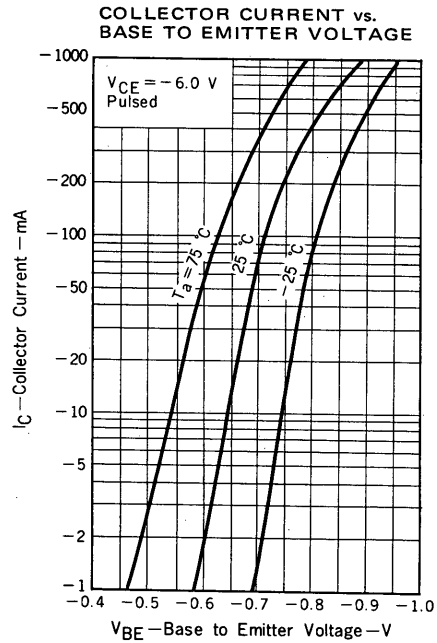
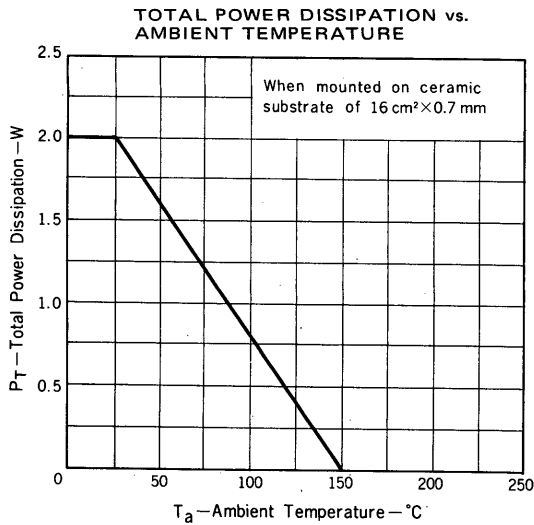
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	I_{CB0}			-100	nA	$V_{CB} = -30$ V, $I_E = 0$
Emitter Cutoff Current	I_{EBO}			-100	nA	$V_{EB} = -5.0$ V, $I_C = 0$
DC Current Gain	h_{FE1}	90	200	400		$V_{CE} = -1.0$ V, $I_C = -100$ mA ***
DC Current Gain	h_{FE2}	50	100			$V_{CE} = -1.0$ V, $I_C = -1.0$ A ***
Collector Saturation Voltage	$V_{CE(sat)}$		-0.25	-0.40	V	$I_C = -1.0$ A, $I_B = -0.10$ A ***
Base Saturation Voltage	$V_{BE(sat)}$		-1.0	-1.2	V	$I_C = -1.0$ A, $I_B = -0.10$ A ***
Base to Emitter Voltage	V_{BE}	-600	-640	-700	mV	$V_{CE} = -6.0$ V, $I_C = -10$ mA ***
Gain Bandwidth Product	f_T		110		MHz	$V_{CE} = -6.0$ V, $I_E = 10$ mA
Output Capacitance	C_{ob}		36		pF	$V_{CB} = -6.0$ V, $I_E = 0$, $f = 1.0$ MHz

***Pulsed: PW ≤ 350 μs, Duty Cycle ≤ 2 %

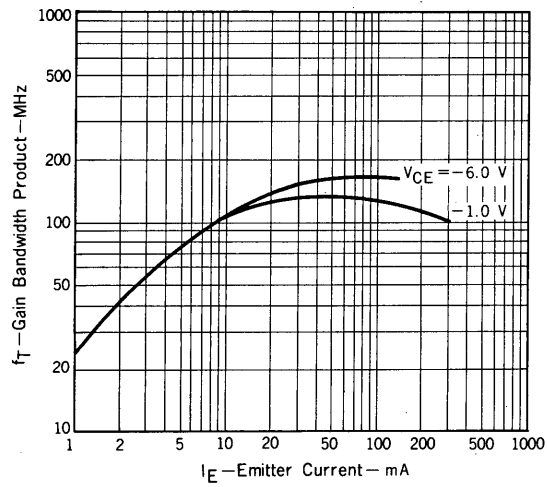
h_{FE} Classification

MARKING	DM	DL	DK
h_{FE1}	90 - 180	135 - 270	200 - 400

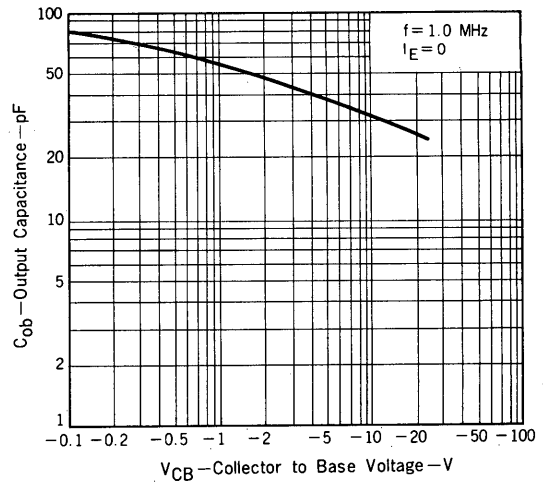
TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)



GAIN BANDWIDTH PRODUCT vs. EMITTER CURRENT



OUTPUT CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	IEI-1207
Semiconductor device package manual.	IEI-1213
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	MF-1134

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Special: Automotive and Transportation equipment, Traffic control systems, Antidisaster systems, Anticrime systems, etc.